

International IR Rectifier

INSULATED GATE BIPOLAR TRANSISTOR

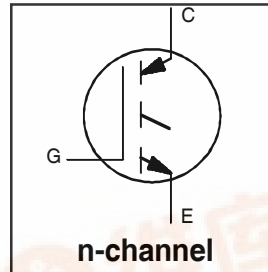
PD -95891

IRG4BH20K-SPbF

Short Circuit Rated
UltraFast IGBT

Features

- High short circuit rating optimized for motor control, $t_{sc} = 10\mu s$ @ $V_{CC} = 720V$, $T_J = 125^\circ C$, $V_{GE} = 15V$
- Combines low conduction losses with high switching speed
- Latest generation design provides tighter parameter distribution and higher efficiency than previous generations
- Industry standard D²Pak package
- Lead-Free



$V_{CES} = 1200V$
$V_{CE(on)} \text{ typ.} = 3.17V$
@ $V_{GE} = 15V, I_C = 5.0A$

Benefits

- As a Freewheeling Diode we recommend our HEXFREDTM ultrafast, ultrasoft recovery diodes for minimum EMI / Noise and switching losses in the Diode and IGBT
- Latest generation 4 IGBT's offer highest power density motor controls possible



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	1200	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	11	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	5.0	
I_{CM}	Pulsed Collector Current ①	22	
I_{LM}	Clamped Inductive Load Current ②	22	
t_{sc}	Short Circuit Withstand Time	10	μs
V_{GE}	Gate-to-Emitter Voltage	± 20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	130	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	60	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	24	
T_J	Operating Junction and	-55 to +150	$^\circ C$
T_{STG}	Storage Temperature Range		

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	2.1	$^\circ C/W$
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	40	
Wt	Weight	6 (0.21)	—	g (oz)

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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)CES}	Collector-to-Emitter Breakdown Voltage	1200	—	—	V	V _{GE} = 0V, I _C = 250μA
V _{(BR)ECS}	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	V _{GE} = 0V, I _C = 1.0A
ΔV _{(BR)CES} /ΔT _J	Temperature Coeff. of Breakdown Voltage	—	1.13	—	V/°C	V _{GE} = 0V, I _C = 2.5mA
V _{CE(ON)}	Collector-to-Emitter Saturation Voltage	—	3.17	4.3	V	I _C = 5.0A V _{GE} = 15V
		—	4.04	—		I _C = 11A See Fig.2, 5
		—	2.84	—		I _C = 5.0A, T _J = 150°C
V _{GE(th)}	Gate Threshold Voltage	3.5	—	6.5		V _{CE} = V _{GE} , I _C = 250μA
ΔV _{GE(th)} /ΔT _J	Temperature Coeff. of Threshold Voltage	—	-10	—	mV/°C	V _{CE} = V _{GE} , I _C = 1mA
g _{fe}	Forward Transconductance ⑤	2.3	3.5	—	S	V _{CE} = 100 V, I _C = 5.0A
I _{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	V _{GE} = 0V, V _{CE} = 1200V
		—	—	2.0		V _{GE} = 0V, V _{CE} = 10V, T _J = 25°C
		—	—	1000		V _{GE} = 0V, V _{CE} = 1200V, T _J = 150°C
I _{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V _{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q _g	Total Gate Charge (turn-on)	—	28	43	nC	I _C = 5.0A
Q _{ge}	Gate - Emitter Charge (turn-on)	—	4.4	6.6		V _{CC} = 400V See Fig.8
Q _{gc}	Gate - Collector Charge (turn-on)	—	12	18		V _{GE} = 15V
t _{d(on)}	Turn-On Delay Time	—	23	—	ns	T _J = 25°C
t _r	Rise Time	—	26	—		I _C = 5.0A, V _{CC} = 960V
t _{d(off)}	Turn-Off Delay Time	—	93	140		V _{GE} = 15V, R _G = 50Ω
t _f	Fall Time	—	270	400		Energy losses include "tail"
E _{on}	Turn-On Switching Loss	—	0.45	—	mJ	See Fig. 9,10,14
E _{off}	Turn-Off Switching Loss	—	0.44	—		
E _{ts}	Total Switching Loss	—	0.89	1.2		
t _{sc}	Short Circuit Withstand Time	10	—	—	μs	V _{CC} = 720V, T _J = 125°C V _{GE} = 15V, R _G = 50Ω
t _{d(on)}	Turn-On Delay Time	—	23	—	ns	T _J = 150°C,
t _r	Rise Time	—	28	—		I _C = 5.0A, V _{CC} = 960V
t _{d(off)}	Turn-Off Delay Time	—	100	—		V _{GE} = 15V, R _G = 50Ω
t _f	Fall Time	—	620	—		Energy losses include "tail"
E _{ts}	Total Switching Loss	—	1.7	—	mJ	See Fig. 10,11,14
L _E	Internal Emitter Inductance	—	7.5	—	nH	Between lead and center of die contact
C _{ies}	Input Capacitance	—	435	—	pF	V _{GE} = 0V
C _{oes}	Output Capacitance	—	44	—		V _{CC} = 30V See Fig. 7
C _{res}	Reverse Transfer Capacitance	—	8.3	—		f = 1.0MHz

Notes:

- ① Repetitive rating; V_{GE} = 20V, pulse width limited by max. junction temperature. (See fig. 13b)
- ② V_{CC} = 80%(V_{CES}), V_{GE} = 20V, L = 10μH, R_G = 50Ω, (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width ≤ 80μs; duty factor ≤ 0.1%.
- ⑤ Pulse width 5.0μs, single shot.

* When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

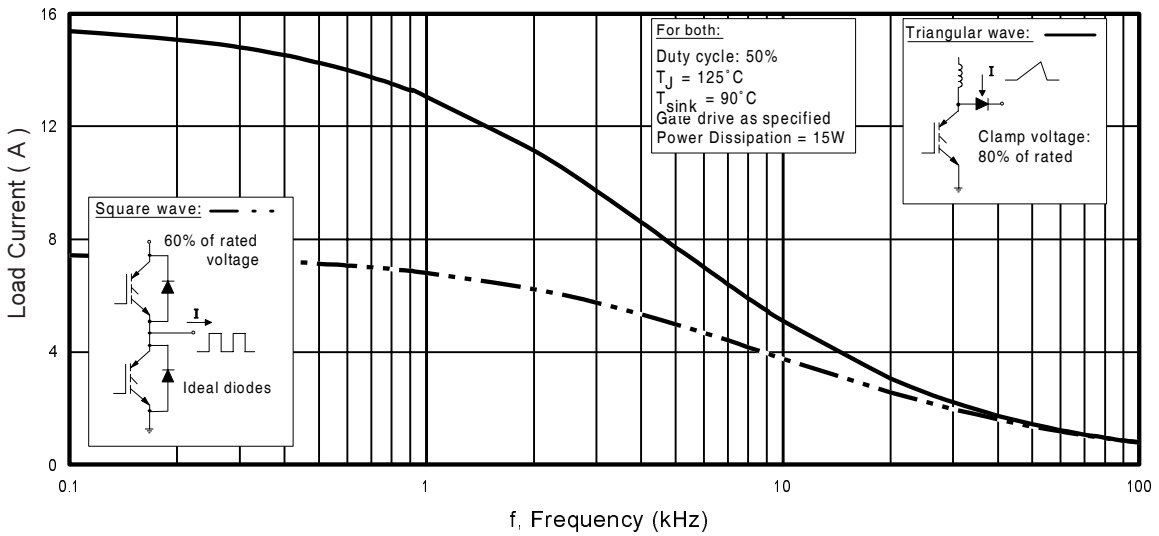


Fig. 1 - Typical Load Current vs. Frequency
 (Load Current = I_{RMS} of fundamental)

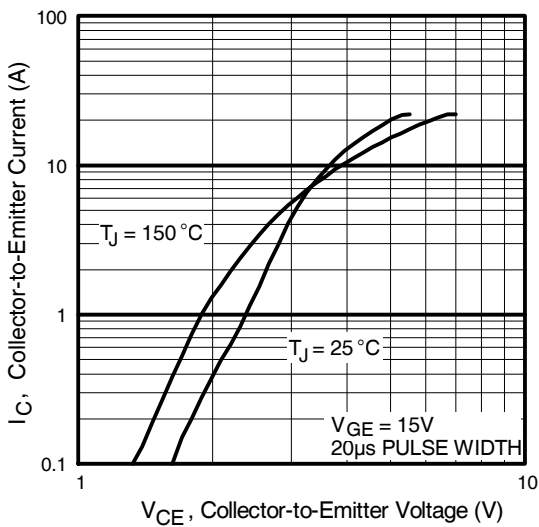


Fig. 2 - Typical Output Characteristics
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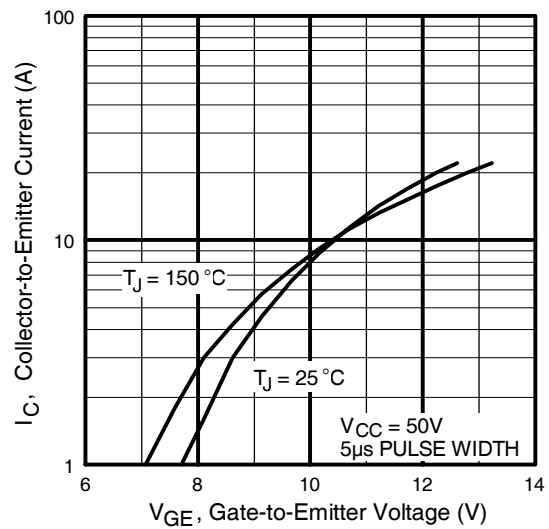


Fig. 3 - Typical Transfer Characteristics

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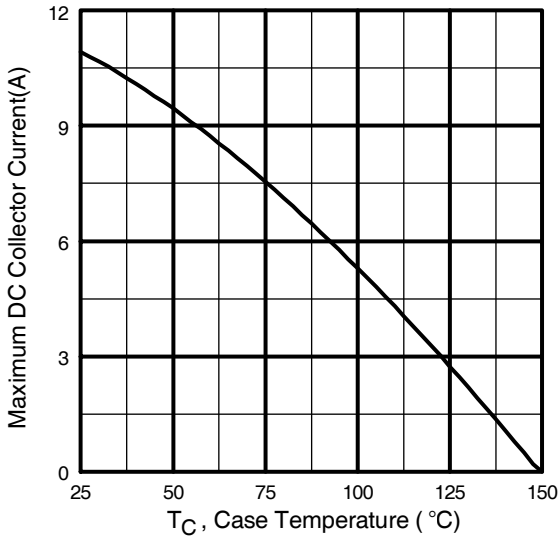


Fig. 4 - Maximum Collector Current vs. Case Temperature

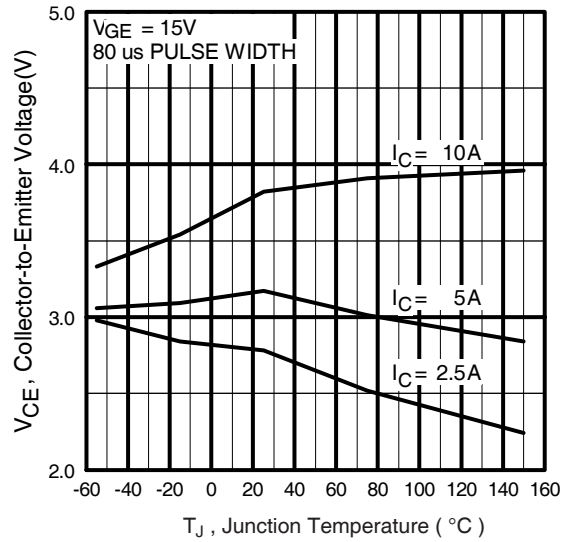


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

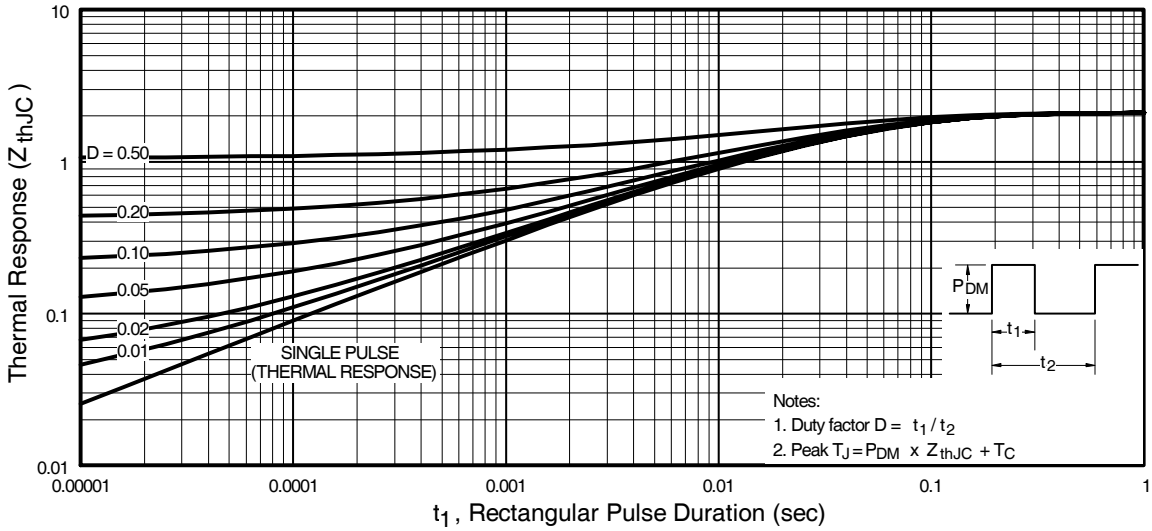


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

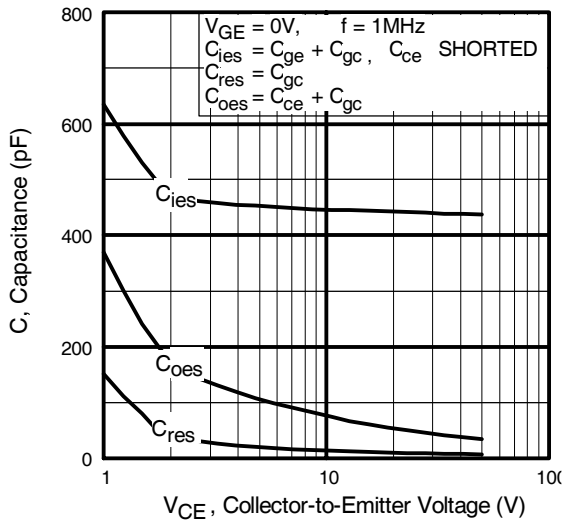


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

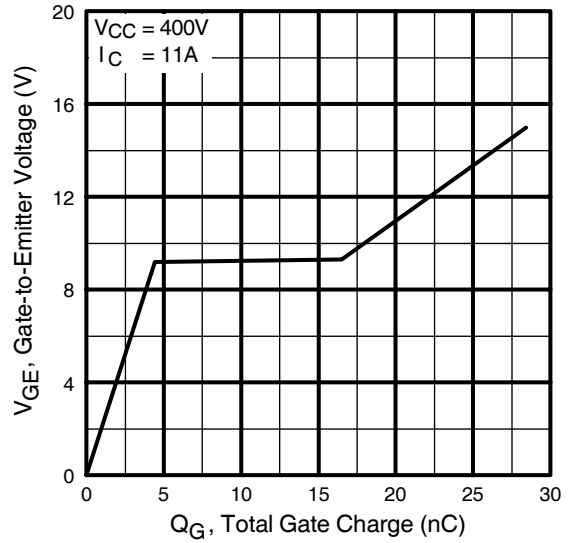


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

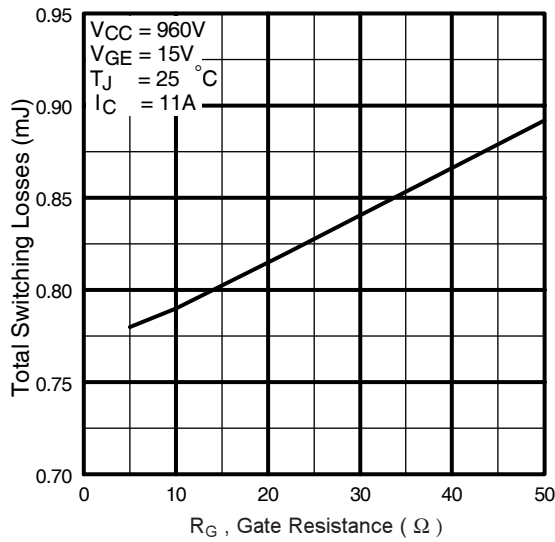


Fig. 9 - Typical Switching Losses vs. Gate Resistance

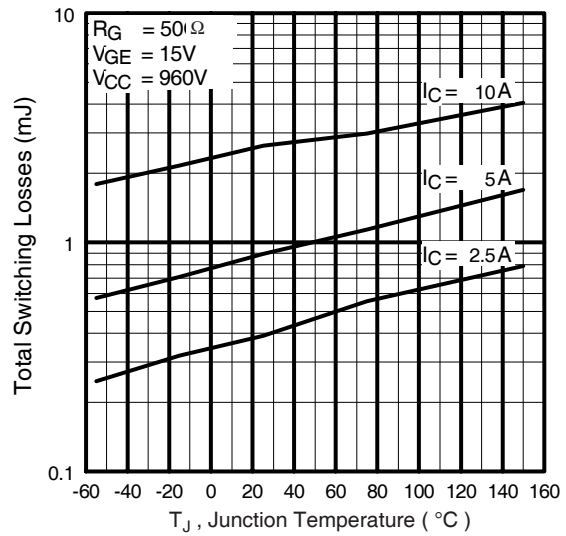


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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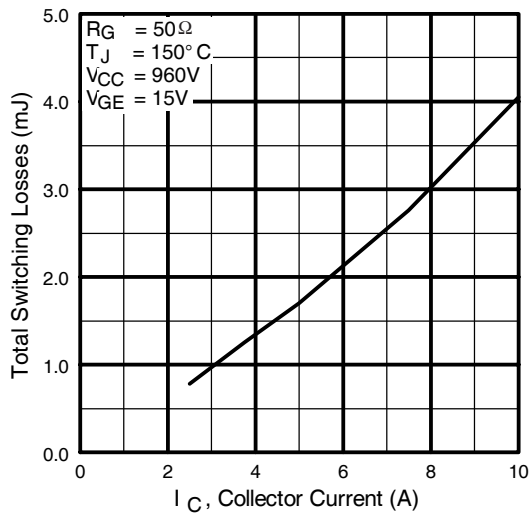


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

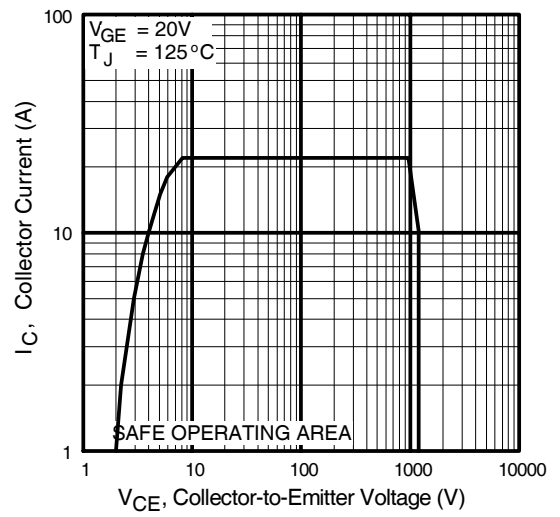


Fig. 12 - Turn-Off SOA

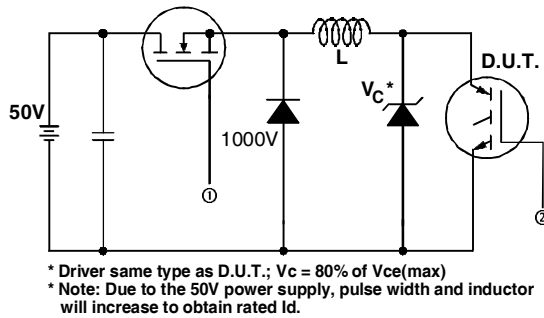


Fig. 13a - Clamped Inductive Load Test Circuit

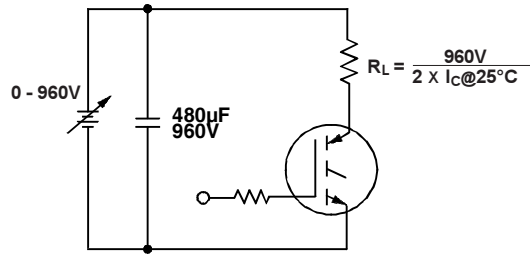


Fig. 13b - Pulsed Collector Current Test Circuit

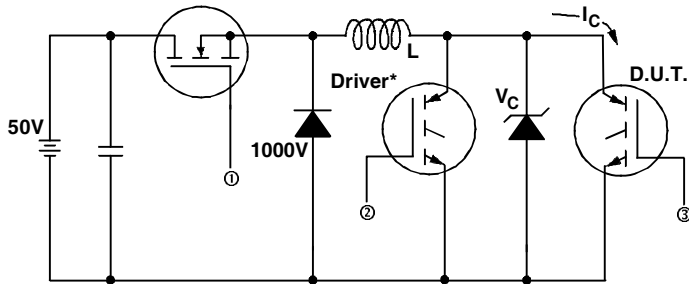


Fig. 14a - Switching Loss Test Circuit

* Driver same type as D.U.T., $V_C = 960V$

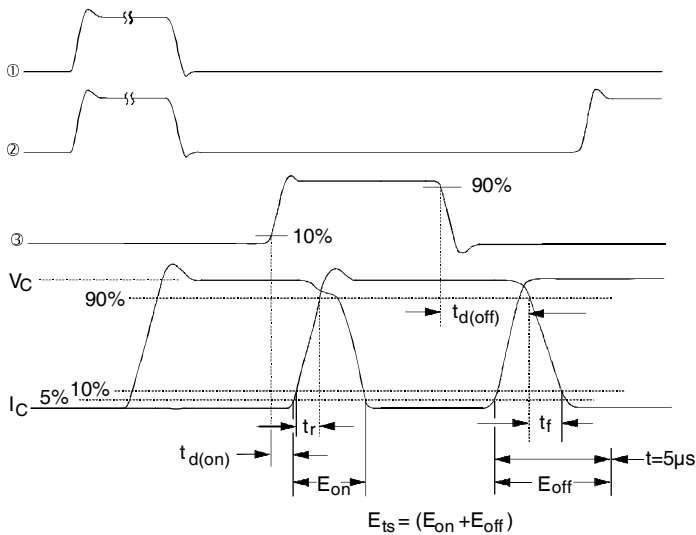


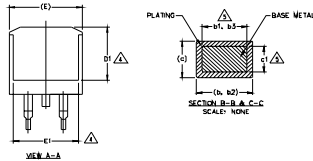
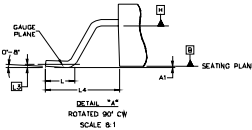
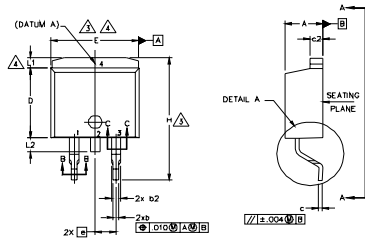
Fig. 14b - Switching Loss Waveforms

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D²Pak Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
7. CONTROLLING DIMENSION: INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	5
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	-	.270	-	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	-	.245	-	4
e	2.54 BSC		.100 BSC		4
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1	-	1.65	-	.066	
L2	1.27	1.78	-	.070	
L3	0.25 BSC		.010 BSC		
L4	4.78	5.28	.188	.208	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2, 4.- DRAIN
- 3.- SOURCE

IGBTs, CoPACK

- 1.- GATE
- 2, 4.- COLLECTOR
- 3.- EMITTER

DIODES

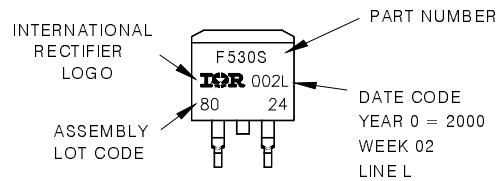
- 1.- ANODE *
- 2, 4.- CATHODE
- 3.- ANODE

* PART DEPENDENT.

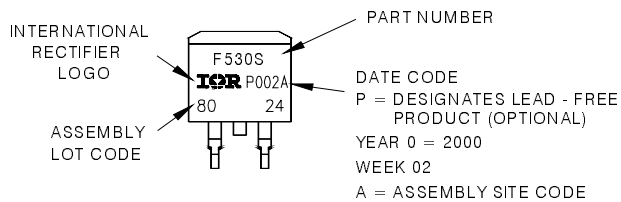
D²Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH LOT CODE 8024 ASSEMBLED ON WW 02, 2000 IN THE ASSEMBLY LINE 'L'

Note: "P" in assembly line position indicates "Lead - Free"

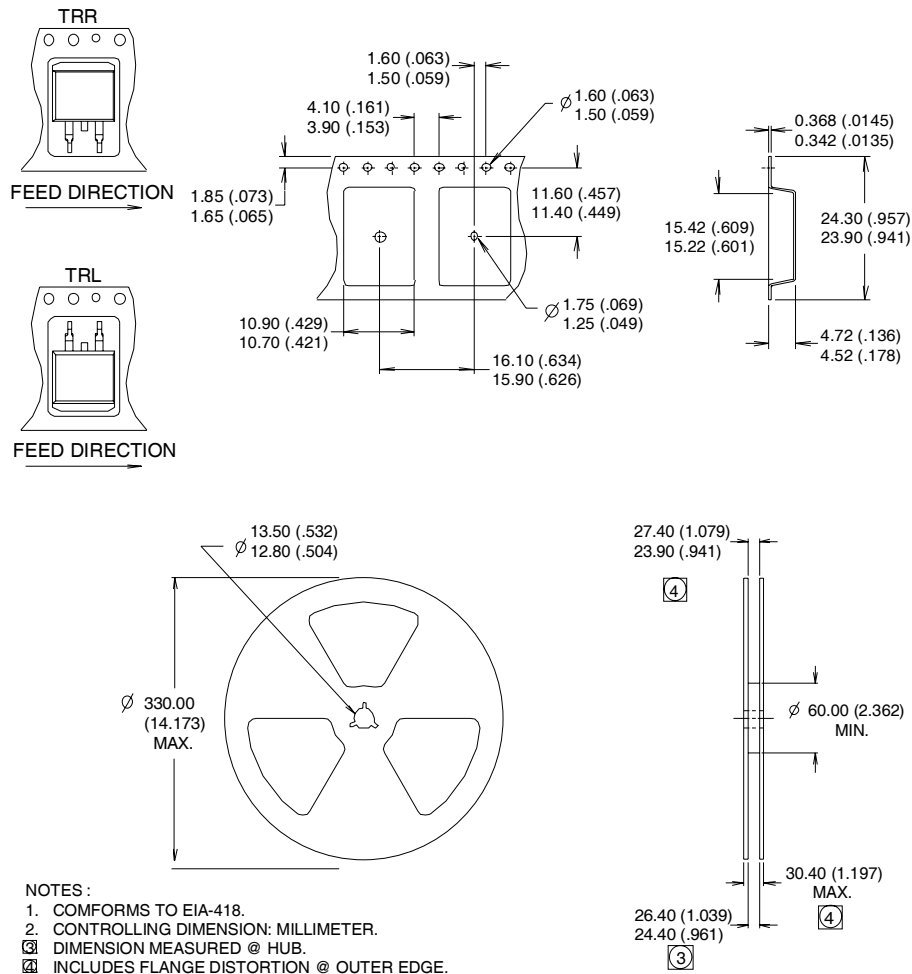


OR



D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



Data and specifications subject to change without notice.

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>